L Number	Hits	Search Text	DB	Time stamp
1	8	(active and clad\$5 and grating and (aperture or	USPAT	2003/10/22 13:21
		window or open\$5) and (insulat\$5 or block\$4) and		
		(electrode with (insulat\$5 or block\$4) with gap))		
		and (DFB or (distibuted feedback))		
2	33	(active and clad\$5 and grating and (aperture or	USPAT	2003/10/22 14:13
		window or open\$5) and (insulat\$5 or block\$4) and		
		(electrode AND (insulat\$5 or block\$4) with gap))		
_		and (DFB or (distributed near1 feedback))		0000110100 1111
3	19	(active and clad\$5 and grating and (aperture or	USPAT	2003/10/22 14:14
		window or open\$5) and (insulat\$5 or block\$4) and		
		(electrode AND (insulat\$5) with gap)) and (DFB or	•	
	235	(distributed near1 feedback))	LICDAT.	2001/10/31 14:04
•	235	(semiconductor near laser) and substrate and grating	USPAT;	2001/10/31 14:04
		and (insulat\$ or nonconductor or non adj conductor	US-PGPUB;	
		or isolat\$) and electrode and (groove or grind or pace	EPO; JPO; DERWENT;	·
		or rut\$ or rote) and clad\$	1	
	170	Manager and setting	IBM_TDB USPAT;	2001/11/01 09:07
· .	172	((semiconductor near laser) and substrate and grating and (insulat\$ or nonconductor or non adj conductor	US-PGPUB;	2001/11/01 09:07
		or isolat\$) and electrode and (groove or grind or pace	EPO; JPO;	
		or rut\$ or rote) and clad\$) and 372/\$	DERWENT;	
		of fully of fole, and claus, and 372/4	IBM TDB	
	7	((semiconductor near laser) and (substrate near (layer	USPAT;	2001/11/01 09:18
	' '	or medium or film or region)) and grating and (layer	US-PGPUB;	2001/11/01 03:10
		near (insulat\$ or nonconductor or non adj conductor	EPO; JPO;	
		or isolat\$)) and (electrode near (layer or medium or	DERWENT;	
		film or region)) and (groove or grind or pace or rut\$	IBM TDB	-
]		or rote) and (clad\$ near (layer or medium or film or		
		region))) and 372/\$		
-	86	((semiconductor near laser) and substrate and grating	USPAT;	2001/11/01 11:31
		and (insulat\$ or nonconductor or non adj conductor	US-PGPUB;	
		or isolat\$) and electrode and (groove or grind or pace	EPO; JPO;	
		or rut\$ or rote) and clad\$) and 372/\$ and	DERWENT;	
		(waveguide near (layer or film or medium or region))	IBM_TDB	
-	4	(((semiconductor near laser) and (substrate near	USPAT;	2001/11/01 09:17
		(layer or medium or film or region)) and grating and	US-PGPUB;	
		(layer near (insulat\$ or nonconductor or non adj	EPO; JPO;	
		conductor or isolat\$)) and (electrode near (layer or	DERWENT;	
		medium or film or region)) and (groove or grind or	IBM_TDB	
		pace or rut\$ or rote) and (clad\$ near (layer or		
		medium or film or region))) and 372/\$) and		
	47	(waveguide near (layer or film or medium or region))	HCDAT.	2001/11/01 00:20
-	41	(((semiconductor near laser) and substrate and	USPAT; US-PGPUB;	2001/11/01 09:26
		grating and (insulat\$ or nonconductor or non adj conductor or isolat\$) and electrode and (groove or	EPO; JPO;	
		grind or pace or rut\$ or rote) and clad\$) and 372/\$	DERWENT;	
		and (waveguide near (layer or film or medium or	IBM TDB	
		region))) and 372/96	.5 ,	
_	4	(semiconductor near laser) and (substrate near layer)	USPAT;	2001/11/01 09:29
		and grating and (layer near (insulat\$ or nonconductor	US-PGPUB;	
		or non adj conductor or isolat*)) and (electrode near	EPO; JPO;	İ
.]		layer) and (groove) and (clad\$ near layer) and 372/\$	DERWENT;	
		and (waveguide near (layer or film or medium or	IBM TDB	
ļ		region))	-	
-	4	(semiconductor near laser) and (substrate near layer)	USPAT;	2001/11/01 09:35
		and grating and (layer near (insulat\$ or nonconductor	US-PGPUB;	
. 1		or non adj conductor or isolat\$)) and (electrode near	EPO; JPO;	
1		layer) and (groove) and (clad\$ near layer) and 372/\$	DERWENT;	
		and (waveguide near layer)	IBM TDB	

-	40	((((semiconductor near laser) and substrate and	USPAT;	2001/11/01 09:38
		grating and (insulat\$ or nonconductor or non adj	US-PGPUB;	
	·	conductor or isolat\$) and electrode and (groove or	EPO; JPO;	
		grind or pace or rut\$ or rote) and clad\$) and 372/\$	DERWENT;	
		and (waveguide near (layer or film or medium or	IBM_TDB	
		region))) and 372/96) and (waveguide near layer)		2004/44/04 45 54
-	8	(semiconductor near laser) and substrate and (grating	USPAT;	2001/11/01 15:51
		same (insulat\$ or nonconductor or non adj conductor	US-PGPUB;	
		or isolat\$) with (groove or grind or pace or rut\$ or	EPO; JPO;	
		rote)) and electrode and clad\$ and 372/\$ and	DERWENT;	
		(waveguide near (layer or film or medium or region))	IBM_TDB	
		and 372/96 and (waveguide near layer)		
-	6	((semiconductor near laser) and substrate and	USPAT;	2001/11/01 13:26
		(grating same (insulat\$ or nonconductor or non adj	US-PGPUB;	
		conductor or isolat\$) with (groove or grind or pace	EPO; JPO;	
		or rut\$ or rote)) and electrode and clad\$ and 372/\$	DERWENT;	
		and (waveguide near (layer or film or medium or	IBM_TDB	
		region)) and 372/96 and (waveguide near layer)) and		
		resonator		
-	2	(semiconductor near laser) and substrate and (grating	USPAT;	2003/05/02 17:07
		same (insulat\$ or nonconductor or non adj conductor	US-PGPUB;	
		or isolat\$) with (groove or grind or pace or rut\$ or	EPO; JPO;	
		rote) same resonator) and electrode and clad\$ and	DERWENT;	
		372/\$ and (waveguide near (layer or film or medium	IBM_TDB	,
		or region)) and 372/96 and (waveguide near layer)		
-	274	DFB and (semiconductor near laser) and active and	USPAT;	2003/05/02 17:08
		clad\$5 and grating and insulat\$4 and electrode	US-PGPUB	
-	32	DFB and (semiconductor near laser) and active and	USPAT;	2003/05/02 17:09
	•	clad\$5 and grating and (insulat\$4 with gap) and	US-PGPUB	
		electrode		
-	28	DFB and (semiconductor near laser) and active and	USPAT	2003/05/02 17:36
		clad\$5 and grating and (insulat\$4 with gap) and	•	
		electrode	•	
-	25	DFB and (semiconductor near laser) and active and	USPAT	2003/05/02 18:14
		clad\$5 and grating and (insulat\$4 with gap) and		
		electrode and contact		
-	3	DFB and (semiconductor near laser) and active and	USPAT	2003/05/02 18:24
		clad\$5 and (grating with InGaAs) and (insulat\$4		
		with gap) and electrode and contact		
-	8	DFB and (semiconductor near laser) and (grating	USPAT	2003/05/02 18:25
		near3 InGaAs)		
•	0	dfb and active and clad\$5 and grating and (aperture	USPAT	2003/10/20 10:14
		or window or open\$5) and (insulat\$5 or block\$4)		
		and (elongat\$3 near gap) and electrode	<u>.</u>	
-	0	dfb and active and clad\$5 and grating and (aperture	US-PGPUB;	2003/10/20 10:15
		or window or open\$5) and (insulat\$5 or block\$4)	EPO; JPO;	
		and (elongat\$3 near gap) and electrode	DERWENT	
-	0	active and clad\$5 and grating and (aperture or	US-PGPUB;	2003/10/20 10:15
		window or open\$5) and (insulat\$5 or block\$4) and	EPO; JPO;	
		(elongat\$3 near1 gap) and electrode	DERWENT	
-	0	active and clad\$5 and grating and (aperture or	US-PGPUB;	2003/10/20 10:15
		window or open\$5) and (insulat\$5 or block\$4) and	EPO; JPO;	
		(elongat\$3 near1 gap) and electrode	DERWENT	
-	569	active and clad\$5 and grating and (aperture or	US-PGPUB;	2003/10/20 10:19
		window or open\$5)	EPO; JPO;	
			DERWENT	
-	407	(active and clad\$5 and grating and (aperture or	US-PGPUB;	2003/10/20 10:19
		window or open\$5)) and (insulat\$5 or block\$4)	EPO; JPO;	
			DERWENT	

-	246	((active and clad\$5 and grating and (aperture or	US-PGPUB;	2003/10/20 10:19
		window or open\$5)) and (insulat\$5 or block\$4))	EPO; JPO;	
		and electrode	DERWENT	
_	0	(((active and clad\$5 and grating and (aperture or	US-PGPUB;	2003/10/20 10:16
		window or open\$5)) and (insulat\$5 or block\$4))	EPO; JPO;	
		and electrode) and (elon\$9 near1 gap)	DERWENT	
_	143	(((active and clad\$5 and grating and (aperture or	US-PGPUB;	2003/10/20 10:18
		window or open\$5)) and (insulat\$5 or block\$4))	EPO; JPO;	'
		and electrode) and (gap)	DERWENT	
_	1194	active and clad\$5 and grating and (aperture or	USPAT	2003/10/20 10:19
		window or open\$5)		
_	1 0	((active and clad\$5 and grating and (aperture or	US-PGPUB;	2003/10/20 10:20
		window or open\$5)) and (insulat\$5 or block\$4))	EPO; JPO;	
		and electrode	DERWENT	
_	840	active and clad\$5 and grating and (aperture or	USPAT	2003/10/20 13:59
		window or open\$5) and (insulat\$5 or block\$4)		
_	527	(active and clad\$5 and grating and (aperture or	USPAT	2003/10/20 10:22
	02.	window or open\$5) and (insulat\$5 or block\$4)) and		
		electrode		
_	0	((active and clad\$5 and grating and (aperture or	USPAT	2003/10/20 10:23
		window or open\$5) and (insulat\$5 or block\$4)) and	00.71.	
		electrode) and (elongat\$4 near2 gap)		
_	296	((active and clad\$5 and grating and (aperture or	USPAT	2003/10/20 13:37
_	250	window or open\$5) and (insulat\$5 or block\$4)) and	JOHA	2000/10/20 10.0/
		electrode) and (gap)		
_	215	(((active and clad\$5 and grating and (aperture or	USPAT	2003/10/20 13:59
_	213	window or open\$5) and (insulat\$5 or block\$4)) and	00171	2000/10/20:10:00
		electrode) and (gap)) and (DFB or (distibuted		
		feedback))		
_	6	(active and clad\$5 and grating and (aperture or	USPAT	2003/10/22 13:54
_	1	window or open\$5) and (insulat\$5 or block\$4) and	031 71	2003/10/22 13.34
		(electrode with (insulat\$5 or block\$4) with gap))		
		and (DFB or (distributed near1 feedback))		
	17	active and clad\$5 and grating and (aperture or	USPAT	2003/10/22 10:05
•	17	window or open\$5) and (insulat\$5 or block\$4) and	USFAT	2003/10/22 10:05
		!		
		(electrode with (insulat\$5 or block\$4) with gap)	l	1